

# 2

## BDC02A Thru BDC02D

**CASE 29-03, STYLE 14  
TO-92 (TO-226AE)**

**ONE WATT  
AMPLIFIER TRANSISTORS**

Refer to BDB02A for graphs.

### **ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)**

Characteristic	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Voltage (IC = 10 mA, IB = 0) BDC02A BDC02B BDC02C BDC02D	V(BR)CEO	45 60 80 100		Vdc
Collector Cutoff Current (VCB = 45 V, IE = 0) (VCB = 60 V, IE = 0) (VCB = 80 V, IE = 0) (VCB = 100 V, IE = 0)	ICBO		0.1 0.1 0.1 0.1	µAdc
Emitter Cutoff Current (IC = 0, VEB = 5.0 V)	IEBO		100	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (IC = 100 mA, VCE = 1 V) (IC = 500 mA, VCE = 2 V)	hFE	40 25	400	
Collector-Emitter Saturation Voltage (IC = 1000 mA, IB = 100 mA)	VCE(sat)		0.7	Vdc
Collector-Emitter on Voltage (IC = 1000 mA, VCE = 1 V)	VBE(on)		1.2	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current Gain Bandwidth Product (IC = 200 mA, VCE = 5 V, f = 100 MHz)	fT	50		MHz
Output Capacitance (VCB = 10 V, IE = 0, f = 1 MHz)	Cob		30	pF

### **MAXIMUM RATINGS**

Rating	Symbol	BDC 02A	BDC 02B	BDC 02C	BDC 02D	Unit
Collector-Emitter Voltage	VCEO	45	60	80	100	Vdc
Collector-Base Voltage	VCBO	45	60	80	100	Vdc
Emitter-Base Voltage	VEBO			5.0		Vdc
Collector Current - Continuous	IC			1.5		Adc
Total Device Dissipation @ TA = 25°C Derate above 25°C	PD			1.0 8.0		Watt mW/°C
Total Device Dissipation @ TC = 25°C Derate above 25°C	PD			2.5 20		Watt mW/°C
Operating and Storage Junction Temperature Range	TJ, Tstg			-55 to +150		°C

### **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>HJC</sub>	50	°C/W
Thermal Resistance, Junction to Ambient	R <sub>HJC</sub>	125	°C/W